





SN74LXC8T245 SCES916A - NOVEMBER 2020 - REVISED MARCH 2023

SN74LXC8T245 8-bit Dual-Supply Bus Transceiver with Configurable Level Shifting and 3-State Outputs

## 1 Features

Texas

INSTRUMENTS

- Fully configurable dual-rail design allows each port to operate from 1.1 V to 5.5 V
- Robust, glitch-free power supply sequencing
- Up to 420-Mbps support for 3.3 V to 5.0 V
- Schmitt-trigger inputs allow for slow or noisy inputs
- I/Os with integrated dynamic pull-down resistors ٠
- help reduce external component count Control inputs with integrated static pull-down
- resistors allow for floating control inputs High drive strength (up to 32 mA at 5 V)
- Low power consumption:
- - 4-µA maximum (25°C)
- 12-μA maximum (–40°C to 125°C)  $V_{CC}$  isolation and  $V_{cc}$  disconnect (I<sub>off-float</sub>) feature
  - If either V<sub>CC</sub> supply is < 100 mV or</li> disconnected, all I/Os get pulled-down and then become high-impedance
- Ioff supports partial-power-down mode operation
- Compatible with LVC family level shifters
- Control logic (DIR and  $\overline{OE}$ ) are referenced to V<sub>CCA</sub>
- Operating temperature from -40°C to +125°C
- Latch-up performance exceeds 100 mA per JESD 78. Class II
- ESD protection exceeds JESD 22
  - 4000-V Human-Body Model
  - 1000-V Charged-Device Model

## 2 Applications

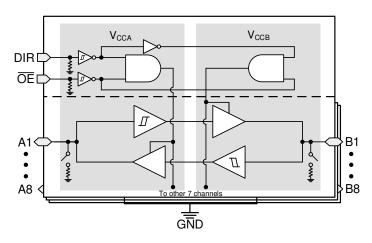
- Eliminate slow or noisy input signals •
- Driving indicator LEDs or buzzers •
- Debouncing a mechanical switch •
- General purpose I/O level shifting
- Push-pull level shifting (UART, SPI, JTAG, and so forth)

## **3 Description**

SN74LXC8T245 is an 8-bit. dual-supply The noninverting bidirectional voltage level translation device. Ax pins and control pins (DIR and  $\overline{OE}$ ) are referenced to  $V_{CCA}$  logic levels, and Bx pins are referenced to V<sub>CCB</sub> logic levels. The A port is able to accept I/O voltages ranging from 1.1 V to 5.5 V, while the B port can accept I/O voltages from 1.1 V to 5.5 V. A high on DIR allows data transmission from A to B and a low on DIR allows data transmission from B to A when  $\overline{OE}$  is set to low. When  $\overline{OE}$  is set to high, both Ax and Bx pins are in the high-impedance state. See Device Functional Modes for a summary of the operation of the control logic.

Package Information (1)									
PART NUMBER	PACKAGE	BODY SIZE (NOM)							
	PW (TSSOP, 24)	7.80 mm × 6.40 mm							
SN74LXC8T245	DGS (VSSOP, 24)	6.10 mm × 3.00 mm							
3N/4LAC01245	RHL (VQFN, 24)	5.50 mm × 3.50 mm							
	RJW (UQFN, 24)	4.00 mm × 2.00 mm							

For all available packages, see the orderable addendum at (1) the end of the data sheet.



**Functional Block Diagram** 





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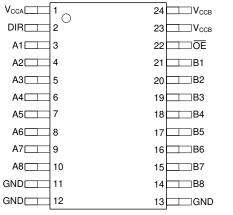
## **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	nanges from Revision * (November 2022) to Revision A (March 2023)	Page
•	Added DGS package information to the data sheet	1



## **5** Pin Configuration and Functions





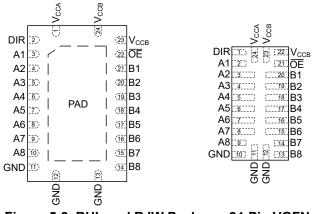


Figure 5-2. RHL and RJW Package, 24-Pin VQFN and UQFN (Transparent Top View)

	PIN										
NAME	PW, DGS, RHL	RJW	TYPE <sup>(1)</sup>	DESCRIPTION							
V <sub>CCA</sub>	1	24	_	A-port supply voltage. 1.1 V $\leq$ V <sub>CCA</sub> $\leq$ 5.5 V.							
DIR	2	1	I	Direction-control signal for all ports. Referenced to V <sub>CCA</sub> .							
A1	3	2	I/O	Input/output A1. Referenced to V <sub>CCA</sub> .							
A2	4	3	I/O	Input/output A2. Referenced to V <sub>CCA</sub> .							
A3	5	4	I/O	Input/output A3. Referenced to V <sub>CCA</sub> .							
A4	6	5	I/O	Input/output A4. Referenced to V <sub>CCA</sub> .							
A5	7	6	I/O	Input/output A5. Referenced to V <sub>CCA</sub> .							
A6	8	7	I/O	Input/output A6. Referenced to V <sub>CCA</sub> .							
A7	9	8	I/O	Input/output A7. Referenced to V <sub>CCA</sub> .							
A8	10	9	I/O	Input/output A8. Referenced to V <sub>CCA</sub> .							
	11	10	_	Ground.							
GND	12	11	_	Ground.							
	13	12	_	Ground.							
B8	14	13	I/O	Input/output B8. Referenced to V <sub>CCB</sub> .							
B7	15	14	I/O	Input/output B7. Referenced to V <sub>CCB</sub> .							
B6	16	15	I/O	Input/output B6. Referenced to V <sub>CCB</sub> .							
B5	17	16	I/O	Input/output B5. Referenced to V <sub>CCB</sub> .							
B4	18	17	I/O	Input/output B4. Referenced to V <sub>CCB</sub> .							
B3	19	18	I/O	Input/output B3. Referenced to V <sub>CCB</sub> .							
B2	20	19	I/O	Input/output B2. Referenced to V <sub>CCB</sub> .							
B1	21	20	I/O	Input/output B1. Referenced to V <sub>CCB</sub> .							
ŌĒ	22	21	I	Output Enable. Pull to GND to enable all outputs. Pull to $V_{CCA}$ to place all outputs in high-impedance mode. Referenced to $V_{CCA}$ .							
V	23	22	_	B-port supply voltage. 1.1 V $\leq$ V <sub>CCB</sub> $\leq$ 5.5 V.							
V <sub>CCB</sub>	24	23	_	B-port supply voltage. 1.1 V $\leq$ V <sub>CCB</sub> $\leq$ 5.5 V.							
PAD	_	_	_	Thermal pad. May be grounded (recommended) or left floating.							

Table 5-1. Pin Functions

(1) I = input, O = output



## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage A		-0.5	6.5	V
V <sub>CCB</sub>	Supply voltage B		-0.5	6.5	V
		I/O Ports (A Port)	-0.5	6.5	
VI	Input Voltage <sup>(2)</sup>	I/O Ports (B Port)	-0.5	6.5	V
		Control Inputs	-0.5	6.5	
Vo	Voltage applied to any output in the high-impedance or power-off	A Port	-0.5	6.5	V
	state <sup>(2)</sup>	B Port	-0.5	6.5	v
V	Value as a set of the answer that the birth on law state $(2)$ $(3)$	A Port	-0.5	V <sub>CCA</sub> + 0.5	V
Vo	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	B Port	-0.5	V <sub>CCB</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	-50		mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	-50		mA
lo	Continuous output current	1	-50	50	mA
	Continuous current through V <sub>CC</sub> or GND	-200	200	mA	
Tj	Junction Temperature		150	°C	
T <sub>stg</sub>	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure beyond the limits listed in Recommended Operating Conditions may affect device reliability.

(2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 6.5 V maximum if the output current rating is observed.

### 6.2 ESD Ratings

			VALUE	UNIT		
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>				
V <sub>(ESD)</sub>		Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000	v		

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1) (2) (3)

				MIN	MAX	UNIT			
V <sub>CCA</sub>	Supply voltage A			1.08	5.5	V			
V <sub>CCB</sub>	Supply voltage B			1.08	5.5	V			
			V <sub>CCO</sub> = 1.1 V		-0.1				
			V <sub>CCO</sub> = 1.4 V		-4				
I	High-level output o	surront	V <sub>CCO</sub> = 1.65 V		-8				
I <sub>OH</sub>		urrent	V <sub>CCO</sub> = 2.3 V		-12	mA			
			V <sub>CCO</sub> = 3 V		-24				
			V <sub>CCO</sub> = 4.5 V	V <sub>CCO</sub> = 4.5 V					
			V <sub>CCO</sub> = 1.1 V		0.1				
			V <sub>CCO</sub> = 1.4 V		4				
	Low-level output c	urront	V <sub>CCO</sub> = 1.65 V		8	mA			
I <sub>OL</sub>		unent	V <sub>CCO</sub> = 2.3 V		12				
			V <sub>CCO</sub> = 3 V		24				
				32					
VI	Input voltage <sup>(3)</sup>		·	0	5.5	V			
V	Output voltage	Active State		0	V <sub>CCO</sub>	v			
Vo	Output voltage	Tri-State		0	5.5	v			
T <sub>A</sub>	Operating free-air	temperature		-40	125	°C			

(1)  $V_{CCI}$  is the  $V_{CC}$  associated with the input port.

(2)  $V_{CCO}$  is the  $V_{CC}$  associated with the output port.

(3) All control inputs and data I/Os of this device have weak pulldowns so that the line is not floating when undefined external to the device. The input leakage from these weak pulldowns is defined by the I<sub>I</sub> specification indicated under *Electrical Characteristics*.

#### 6.4 Thermal Information

	THERMAL METRIC <sup>(1)</sup>	IETRIC <sup>(1)</sup> PW (TSSOP) RHL (VQFN) DGS				UNIT
		24 PINS	24 PINS	24 PINS	24 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	99.6	47.4	86.2	118.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	43.7	42.6	34.6	61.2	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	54.7	25.1	47.2	49.9	°C/W
Y <sub>JT</sub>	Junction-to-top characterization parameter	6.4	2.7	1.5	3.3	°C/W
Y <sub>JB</sub>	Junction-to-board characterization parameter	54.3	25.1	46.9	49.7	°C/W
R <sub>0JC(bottom)</sub>	Junction-to-case (bottom) thermal resistance	n/a	14.9	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

## **6.5 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2)</sup>

		TEST				0	peratir	ng free	air temperat	ure (T	a)	
PARAMETER		CONDITIONS			2	25°C		C to 85°C	<b>-40°</b>	UN		
					MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP MAX	
			1.1 V	1.1 V				0.44	0.88	0.44	0.88	
			1.4 V	1.4 V				0.60	0.98	0.60	0.98	
		Data Inputs	1.65 V	1.65 V				0.76	1.13	0.76	1.13	
		(Ax, Bx) (Referenced to	2.3 V	2.3 V				1.08	1.56	1.08	1.56	v
		V <sub>CCI</sub> )	3 V	3 V				1.48	1.92	1.48	1.92	
	Positive-		4.5 V	4.5 V				2.19	2.74	2.19	2.74	
,	going input-		5.5 V	5.5 V				2.65	3.33	2.65	3.33	
V <sub>T+</sub>	threshold		1.1 V	1.1 V				0.44	0.88	0.44	0.88	
	voltage		1.4 V	1.4 V				0.60	0.98	0.60	0.98	
		Control Inputs	1.65 V	1.65 V				0.76	1.13	0.76	1.13	
		(OE, DIR) (Referenced to	2.3 V	2.3 V				1.08	1.56	1.08	1.56	V
		V <sub>CCA</sub> )	3 V	3 V				1.48	1.92	1.48	1.92	
			4.5 V	4.5 V				2.19	2.74	2.19	2.74	
			5.5 V	5.5 V				2.65	3.33	2.65	3.33	
			1.1 V	1.1 V				0.17	0.48	0.17	0.48	
		Data Inputs (Ax, Bx) (Referenced to V <sub>CCI</sub> )	1.4 V	1.4 V				0.28	0.59	0.28	0.59	
			1.65 V	1.65 V				0.35	0.69	0.35	0.69	v
			2.3 V	2.3 V				0.56	0.97	0.56	0.97	
			3 V	3 V				0.89	1.5	0.89	1.5	
	Negative- going input- threshold		4.5 V	4.5 V				1.51	1.97	1.51	1.97	
			5.5 V	5.5 V				1.88	2.4	1.88	2.4	
V <sub>T-</sub>		Control Inputs (OE, DIR) (Referenced to V <sub>CCA</sub> )	1.1 V	1.1 V				0.17	0.48	0.17	0.48	
	voltage		1.4 V	1.4 V				0.28	0.6	0.28	0.6	
			1.65 V	1.65 V				0.35	0.71	0.35	0.71	V
			2.3 V	2.3 V				0.56	1	0.56	1	
			3 V	3 V				0.89	1.5	0.89	1.5	
			4.5 V	4.5 V				1.51	2	1.51	2	
			5.5 V	5.5 V				1.88	2.46	1.88	2.46	1
			1.1 V	1.1 V				0.2	0.4	0.2	0.4	
			1.4 V	1.4 V				0.25	0.5	0.25	0.5	
		Data Inputs	1.65 V	1.65 V				0.3	0.55	0.3	0.55	4
		(Ax, Bx)	2.3 V	2.3 V				0.38	0.65	0.38	0.65	4
		(Referenced to V <sub>CCI</sub> )	3 V	3 V				0.46	0.72	0.46	0.72	1
		001/	4.5 V	4.5 V				0.58	0.93	0.58	0.93	-
	Input- threshold		5.5 V	5.5 V				0.69	1.06	0.69	1.06	4
ΔV <sub>T</sub>	hysteresis		1.1 V	1.1 V				0.2	0.4	0.2	0.4	
	$(V_{T^+} - V_{T^-})$		1.4 V	1.4 V				0.25	0.5	0.25	0.5	4
		Control Inputs	1.65 V	1.65 V				0.3	0.55	0.3	0.55	-
		(OE, DIR)	2.3 V	2.3 V				0.38	0.65	0.38	0.65	V
		(Referenced to V <sub>CCA</sub> )	3 V	3 V				0.46	0.72	0.46	0.72	
		- CCA/	4.5 V	4.5 V				0.58	0.93	0.58	0.93	
			4.5 V 5.5 V	5.5 V				0.69	1.06	0.69	1.06	4



### 6.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)<sup>(1) (2)</sup>

		TEOT			Operating free-air temperature (T <sub>A</sub> )								
PA	RAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	25°C			-40°	C to 85°C	-40°	C to 125°C	וואט	
					MIN	TYP	MAX	MIN	TYP MAX		ΤΥΡ ΜΑλ	۲ ۲	
		I <sub>OH</sub> = −100 μA	1.1 V - 5.5 V	1.1 V - 5.5 V				V <sub>CCO</sub> - 0.1		V <sub>CCO</sub> - 0.1			
	High-level	I <sub>OH</sub> = -4 mA	1.4 V	1.4 V				1		1			
V <sub>OH</sub>	output	I <sub>OH</sub> = -8 mA	1.65 V	1.65 V				1.2		1.2		V	
	voltage <sup>(3)</sup>	I <sub>OH</sub> = -12 mA	2.3 V	2.3 V				1.9		1.9			
		I <sub>OH</sub> = -24 mA	3 V	3 V				2.4		2.4			
		I <sub>OH</sub> = -32 mA	4.5 V	4.5 V				3.8		3.8		7	
		I <sub>OL</sub> = 100 μA	1.1 V - 5.5 V	1.1 V - 5.5 V					0.1		0.1		
		I <sub>OL</sub> = 4 mA	1.4 V	1.4 V					0.3		0.3	3	
	Low-level	I <sub>OL</sub> = 8 mA	1.65 V	1.65 V					0.45		0.45	5	
V <sub>OL</sub>	output voltage <sup>(4)</sup>	I <sub>OL</sub> = 12 mA	2.3 V	2.3 V					0.3		0.3		
		I <sub>OL</sub> = 24 mA	3 V	3 V					0.55		0.55	5	
		I <sub>OL</sub> = 32 mA	4.5 V	4.5 V					0.55		0.55	5	
I	Input leakage	Control inputs (DIR, $\overline{OE}$ ) V <sub>I</sub> = V <sub>CCA</sub> or GND	1.1 V - 5.5 V	1.1 V - 5.5 V	-0.1		1.5	-0.1	2	-0.1	2	2 μA	
	current	Data Inputs (Ax, Bx) V <sub>I</sub> = V <sub>CCI</sub> or GND	1.1 V - 5.5 V	1.1 V - 5.5 V	-0.3		0.3	-1	1	-2	2	<u>2</u> μΑ	
	Partial power	A Port or B Port	0 V	0 V - 5.5 V	-1.5		1.5	-2	2	-2.5	2.5		
I <sub>off</sub>	down current	V <sub>I</sub> or V <sub>O</sub> = 0 V - 5.5 V	0 V - 5.5 V	0 V	-1.5		1.5	-2	2	-2.5	2.5	μΑ i	
	Floating		Floating (6)	0 V - 5.5 V	-1.5		1.5	-2	2	-2.5	2.5	5	
I <sub>off-float</sub>	supply Partial power down current	A Port or B Port V <sub>I</sub> or V <sub>O</sub> = GND	0 V - 5.5 V	Floating <sup>(6)</sup>	-1.5		1.5	-2	2	-2.5	2.5	μA	
I <sub>OZ</sub>	Tri-state output current (5)	A or B Port: $V_1 = V_{CC1}$ or GND $V_0 = V_{CC0}$ or GND $\overline{OE} = V_{T+(MAX)}$	1.1 V - 5.5 V	1.1 V - 5.5 V	-0.3		0.3	-1	1	-2	2	2 µA	
			1.1 V - 5.5 V	1.1 V - 5.5 V			2		4		8	3	
		$V_I = V_{CCI}$ or GND $I_O = 0$	0 V	5.5 V	-0.2			-0.5		-1			
I <sub>CCA</sub>	V <sub>CCA</sub> supply current	10 - 0	5.5 V	0 V			1		2		4	μA	
		V <sub>I</sub> = GND I <sub>O</sub> = 0	5.5 V	Floating <sup>(6)</sup>			2		4		8	3	
			1.1 V - 5.5 V	1.1 V - 5.5 V			2		4		6	3	
		$V_I = V_{CCI}$ or GND	0 V	5.5 V			1		2		4		
I <sub>CCB</sub>	V <sub>CCB</sub> supply current	I <sub>O</sub> = 0	5.5 V	0 V	-0.2			-0.5		-1		μA	
	current	$V_1 = GND$ $I_0 = 0$	Floating <sup>(6)</sup>	5.5 V			2		4			3	
I <sub>CCA</sub> + I <sub>CCB</sub>	Combined supply current	$V_{I} = V_{CCI}$ or GND $I_{O} = 0$	1.1 V - 5.5 V	1.1 V - 5.5 V			4		8		12	<u>2</u> μΑ	

## 6.5 Electrical Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

					0	peratir	ng free	-air te	mperat	ure (T <sub>A</sub>	)			
PAI	RAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>		25°C		–40°C to 85°C			–40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
ΔI <sub>CCA</sub>	V <sub>CCA</sub> additional supply	$\begin{array}{l} \mbox{Control inputs} \\ \mbox{(DIR, $\overline{OE}$)$:} \\ \mbox{V}_{I} = \mbox{V}_{CCA} - 0.6 \mbox{ V} \\ \mbox{A port} = \mbox{VCCA} \\ \mbox{or $GND$} \\ \mbox{B Port} = \mbox{open} \end{array}$	3.0 V - 5.5 V	3.0 V - 5.5 V						50			75	μA
	current per input	A Port: $V_I = V_{CCA}$ - 0.6 V DIR = $V_{CCA}$ , B Port = open	3.0 V - 5.5 V	3.0 V - 5.5 V						50			75	
ΔI <sub>CCB</sub>	V <sub>CCB</sub> additional supply current per input	B Port: $V_I = V_{CCB}$ - 0.6 V DIR = GND, A Port = open	3.0 V - 5.5 V	3.0 V - 5.5 V						50			75	μA
C <sub>i</sub>	Control Input Capacitance	V <sub>I</sub> = 3.3 V or GND	3.3 V	3.3 V		2.6				5			5	pF
C <sub>io</sub>	Data I/O Capacitance	$\overline{OE}$ = V <sub>CCA</sub> , V <sub>O</sub> = 1.65V DC +1 MHz -16 dBm sine wave	3.3 V	3.3 V		5.8				10			10	pF

 $V_{\text{CCI}}$  is the  $V_{\text{CC}}$  associated with the input port. (1)

(1)  $V_{CCI}$  is the  $V_{CC}$  associated with the input port. (2)  $V_{CCO}$  is the  $V_{CC}$  associated with the output port. (3) Tested at  $V_I = V_{T+(MAX)}$ . (4) Tested at  $V_I = V_{T-(MIN)}$ . (5) For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current. (5) For I/O ports, the parameter I<sub>OZ</sub> includes the input leakage current.

(6) Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10 nA.



## 6.6 Switching Characteristics, V<sub>CCA</sub> = 1.2 ± 0.1 V

									B-PORT S	UPPLY	VOLTAGE (V	(ссв)						
1	PARAMETER	FROM	то	TEST CONDITIONS	1.2 ± 0.1	V	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	V	3.3	3 ± 0.3 V	5	.0 ± 0.5	V	UNIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX	
		А	в	–40°C to 85°C	10	65	10	31	7	25	7	24	5	22	5		21	
+	Propagation	^		–40°C to 125°C	10	70	10	33	7	27	7	26	5	24	5		23	ns
t <sub>pd</sub>	delay	В	A	–40°C to 85°C	10	62	10	55	10	49	8	42	8	40	8		39	115
			–40°C to 125°C	10	68	10	60	10	54	8	47	8	45	8		44		
		OE A	٨	–40°C to 85°C	20	64	20	64	20	64	20	64	20	64	20		64	
+	Disable time	UE	DE A	–40°C to 125°C	20	69	20	69	20	69	20	69	20	69	20		69	ns
t <sub>dis</sub>	Disable time		в	–40°C to 85°C	20	80	20	62	20	54	20	48	20	47	20		45	115
				–40°C to 125°C	20	85	20	67	20	59	20	52	20	50	20		48	
		ŌE A	٨	–40°C to 85°C	20	90	20	91	20	91	20	91	20	90	20		90	
+	Enable time			–40°C to 125°C	20	97	20	98	20	97	20	96	20	96	20		96	
t <sub>en</sub>			P	–40°C to 85°C	20	95	20	57	15	48	10	38	10	36	10		36	ns
			–40°C to 125°C	20	100	20	61	15	53	10	42	10	39	10		39		



## 6.7 Switching Characteristics, $V_{CCA} = 1.5 \pm 0.1 V$

	TEST			B-PORT SUPPLY VOLTAGE (V <sub>CCB</sub> )														
	PARAMETER	FROM	то		1.2 ± 0.1	V	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	2 V	3.	3 ± 0.3 V	5	.0 ± 0.5 '	v	UNIT
					MIN TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX							
		А	В	–40°C to 85°C	10	52	5	25	5	23	5	17	5	14	3		13	
+	Propagation	^		–40°C to 125°C	10	57	5	26	5	23	5	18	5	16	3		14	ns
t <sub>pd</sub>	delay	В	3 A -	–40°C to 85°C	8	36	7	28	7	26	5	20	5	18	5		17	115
		В		–40°C to 125°C	8	40	7	29	7	26	5	22	5	20	5		18	
		ŌĒ	^	–40°C to 85°C	15	40	15	40	15	40	15	40	15	40	15		40	
	Disable time	UE	DE A	-40°C to 125°C	15	44	15	44	15	44	15	44	15	44	15		44	ns
t <sub>dis</sub>			В	–40°C to 85°C	20	69	20	50	15	45	15	35	15	34	14		31	115
		ŌĒ		–40°C to 125°C	20	74	20	54	15	48	15	39	15	37	14		33	
		Œ	^	–40°C to 85°C	15	48	15	48	15	48	15	48	15	48	15		48	
	Enable time	-	A	–40°C to 125°C	15	52	15	52	15	52	15	52	15	52	15		52	<b>n</b> 0
t <sub>en</sub>			B	–40°C to 85°C	20	85	15	50	15	40	10	31	10	26	10		24	ns
		DE B	–40°C to 125°C	20	91	15	54	15	44	10	33	10	29	10		26		



## 6.8 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15 V$

									B-PORT S	UPPLY	VOLTAGE (	/ <sub>ссв</sub> )						
	PARAMETER	FROM	то	TEST CONDITIONS	1.2 ± 0.1	V	1.5 ± 0.1	v	1.8 ± 0.1	5 V	2.5 ± 0.2	2 V	3.	3 ± 0.3 V	5	.0 ± 0.5	v	UNIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX	
		٨	в	–40°C to 85°C	8	50	6	21	6	18	4	14	4	11	2		10	
+	Propagation	A		–40°C to 125°C	8	53	6	23	6	20	4	15	4	12	2		11	ns
t <sub>pd</sub>	delay	В	A	–40°C to 85°C	5	32	5	21	5	19	4	17	4	15	4		15	115
			–40°C to 125°C	5	33	5	23	5	21	4	18	4	16	4		16		
		ŌĒ	Δ	–40°C to 85°C	10	34	10	33	10	33	10	33	10	33	10		33	
+	Disable time	OL	DE A	–40°C to 125°C	10	36	10	35	10	35	10	35	10	35	10		35	ns
t <sub>dis</sub>	Disable time	в	–40°C to 85°C	20	64	15	45	15	40	12	31	12	31	10		26	115	
		OL		–40°C to 125°C	20	69	15	49	15	44	12	33	12	38	10		28	
		OE A	٨	–40°C to 85°C	10	38	10	38	10	38	10	38	10	38	10		38	
	Enable time $\overline{OE}$ A			–40°C to 125°C	10	40	10	40	10	40	10	40	10	40	10		40	
t <sub>en</sub>			B	–40°C to 85°C	20	84	15	47	10	38	10	29	10	25	8		23	ns
			–40°C to 125°C	20	89	15	51	10	42	10	30	10	26	8		25		



## 6.9 Switching Characteristics, V<sub>CCA</sub> = 2.5 ± 0.2 V

	TEST			B-PORT SUPPLY VOLTAGEe (V <sub>CCB</sub> )														
1	PARAMETER	FROM	то		1.2 ± 0.1	V	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	2 V	3.	3 ± 0.3 V	5	.0 ± 0.5	v	UNIT
					MIN TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX							
		А	в	–40°C to 85°C	7	40	5	21	4	16	3	12	3	10	3		8	
	Propagation	^		–40°C to 125°C	7	45	5	22	4	17	3	13	3	11	3		9	<b>n</b> 0
t <sub>pd</sub>	delay	B		–40°C to 85°C	5	26	5	16	5	15	4	12	3	11	3		10	ns
		В		-40°C to 125°C	5	28	5	17	5	15	4	13	3	12	3		11	
		<del>de</del> a	٨	–40°C to 85°C	10	24	10	24	10	24	10	24	10	22	10		24	
	Disable time	UE	DE A	-40°C to 125°C	10	26	10	26	10	24	10	24	10	24	10		24	<b>n</b> 0
t <sub>dis</sub>	Disable time		в	–40°C to 85°C	15	56	15	41	12	34	12	25	10	24	10		21	ns
		OL		–40°C to 125°C	15	62	15	44	12	37	12	29	10	26	10		22	
		Œ	Δ	–40°C to 85°C	8	25	8	25	8	25	8	25	8	25	8		25	
	Enable time	-		–40°C to 125°C	8	27	8	27	8	27	8	27	8	27	8		27	<b>n</b> 0
t <sub>en</sub>			P	–40°C to 85°C	20	80	15	46	10	34	10	25	5	23	5		18	ns
				–40°C to 125°C	20	86	15	48	10	37	10	27	5	25	5		20	



## 6.10 Switching Characteristics, V<sub>CCA</sub> = 3.3 ± 0.3 V

									B-PORT S	UPPLY	VOLTAGE (	√ <sub>ссв</sub> )						
	PARAMETER	FROM	то	TEST CONDITIONS	1.2 ± 0.1	V	1.5 ± 0.1	V	1.8 ± 0.1	5 V	2.5 ± 0.2	2 V	3.	3 ± 0.3 V	5	5.0 ± 0.5	V	UNIT
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN TYP	MAX	MIN	TYP MAX		TYP	MAX	
		٨	в	–40°C to 85°C	8	41	6	19	4	15	3	10	3		9 2		6.5	
+	Propagation	A		–40°C to 125°C	8	43	6	21	4	16	3	11	3	1	) 2		7.5	ns
t <sub>pd</sub>	delay	В	А	–40°C to 85°C	5	22	5	15	4	12	3	10	3		9 3		8.5	115
			–40°C to 125°C	5	24	5	16	4	13	3	11	3	1	) 3		9		
		OE /	^	–40°C to 85°C	9	19	9	19	9	19	8	19	8	1	8		19	
<b>t</b>	Disable time	OL	E A -	–40°C to 125°C	9	20	9	20	9	20	8	20	8	2	) 8		20	ns
t <sub>dis</sub>			в	–40°C to 85°C	15	52	15	38	12	32	10	23	10	2	2 9		18	115
		OL		–40°C to 125°C	15	59	15	41	12	35	10	26	10	2	3 9		20	
			Δ	–40°C to 85°C	5	20	5	20	5	20	5	20	5	2	) 5		20	
+	Enable time $\overline{OE}$ A $\overline{OE}$ B	0E		–40°C to 125°C	5	22	5	22	5	22	5	22	5	2	2 5		22	
t <sub>en</sub>			D	–40°C to 85°C	20	80	15	43	10	34	5	24	5	1	9 5		16	ns
		OE B		–40°C to 125°C	20	85	15	46	10	36	5	27	5	2	1 5		18	



## 6.11 Switching Characteristics, $V_{CCA} = 5.0 \pm 0.5 V$

	TEST			B-PORT SUPPLY VOLTAGE (V <sub>CCB</sub> )															
	PARAMETER	FROM	то		1.2 ± 0.1	I V	1.5 ± 0.1	V	1.8 ± 0	.15 V	2.5	± 0.2 V	3.	3 ± 0.3 V	5	.0 ± 0.5	V	UNIT	
					MIN TYP	MAX	MIN TYP	MAX	MIN TYP	P MAX	MIN .	TYP MAX	MIN	TYP MAX	MIN	TYP	MAX		
		А	В	–40°C to 85°C	8	38	6	15	3	14	3	9.5	2	8	2		6		
+	Propagation	A	D	–40°C to 125°C	8	42	6	17	3	15	3	10.5	2	8.5	2		7	-	
t <sub>pd</sub>	delay	В	A	–40°C to 85°C	5	22	4	13	3	10.5	3	8	2	7.5	2		7	ns	
				–40°C to 125°C	5	24	4	15	3	11.5	3	8.5	2	8	2		7.5		
	ŌĒ		–40°C to 85°C	7	15	5	15	5	15	5	15	5	14	5		14			
+	Disable time		OE A	-40°C to 125°C	7	16	5	16	5	16	5	16	5	15	5		15	-	
t <sub>dis</sub>	Disable little	ŌĒ	в	–40°C to 85°C	15	52	12	33	10	31	10	22	10	21	5		16	ns	
		UE	D	-40°C to 125°C	15	56	12	37	10	35	10	24	10	23	5		18		
		_		A	–40°C to 85°C	5	15	5	15	5	15	5	15	5	15	5		15	
	OE Enable time OE		A	–40°C to 125°C	5	16	5	16	5	16	5	16	5	16	5		16		
t <sub>en</sub>			в	–40°C to 85°C	20	80	15	44	10	33	5	24	5	18	5		15	ns	
		UE	ט	–40°C to 125°C	20	85	15	48	10	35	5	26	5	20	5		17		



## 6.12 Switching Characteristics: T<sub>sk</sub>, T<sub>MAX</sub>

over operating free-air temperature range (unless otherwise noted)

		· ·			Operati	ng temp (T <sub>A</sub> )	
PARAMETER	TEST CONDI	TIONS	V <sub>CCI</sub>	V <sub>cco</sub>	-40°0	C to 125°C	UNIT
					MIN	TYP MA	X
			3.0 V – 3.6 V	4.5 V – 5.5 V	200	420	
			1.65 V – 1.95 V	4.5 V – 5.5 V	100	200	
		Lin Translation	1.1 V – 1.3 V	4.5 V – 5.5 V	20	40	
		Up Translation	1.65 V – 1.95 V	3.0 V – 3.6 V	100	210	
	50% Duty Cycle Input		1.1 V – 1.3 V	3.0 V – 3.6 V	10	20	
T <sub>MAX</sub> - Maximum	One channel switching		1.1 V – 1.3 V	1.65 V – 1.95 V	5	10	Mhna
Data Rate	20% of pulse > $0.7*V_{CCO}$		4.5 V – 5.5 V	3.0 V – 3.6 V	100	210	— Mbps
	20% of pulse < $0.3^{*}V_{CCO}$		4.5 V – 5.5 V	1.65 V – 1.95 V	50	75	
		Down Translation	4.5 V – 5.5 V	1.1 V – 1.3 V	15	30	
		Down translation	3.0 V – 3.6 V	1.65 V – 1.95 V	40	75	
			3.0 V – 3.6 V	1.1 V – 1.3 V	10	20	
			1.65 V – 1.95 V	1.1 V – 1.3 V	5	10	
			3.0 V – 3.6 V	4.5 V – 5.5 V		C	.5
			1.65 V – 1.95 V	4.5 V – 5.5 V			1
		Up Translation	1.1 V – 1.3 V	4.5 V – 5.5 V		1	.5
		Op Translation	1.65 V – 1.95 V	3.0 V – 3.6 V			1
	Timing skew between		1.1 V – 1.3 V	3.0 V – 3.6 V		1	.5
t <sub>sk</sub> - Output skew	any two switching		1.1 V – 1.3 V	1.65 V – 1.95 V			2
i <sub>sk</sub> - Output skew	outputs within the same		4.5 V – 5.5 V	3.0 V – 3.6 V		C	.5 ns
	device		4.5 V – 5.5 V	1.65 V – 1.95 V			1
		Down Translation	4.5 V – 5.5 V	1.1 V – 1.3 V		1	.5
		Down Translation	3.0 V – 3.6 V	1.65 V – 1.95 V			1
			3.0 V – 3.6 V	1.1 V – 1.3 V		1	.5
			1.65 V – 1.95 V	1.1 V – 1.3 V			2

### 6.13 Operating Characteristics

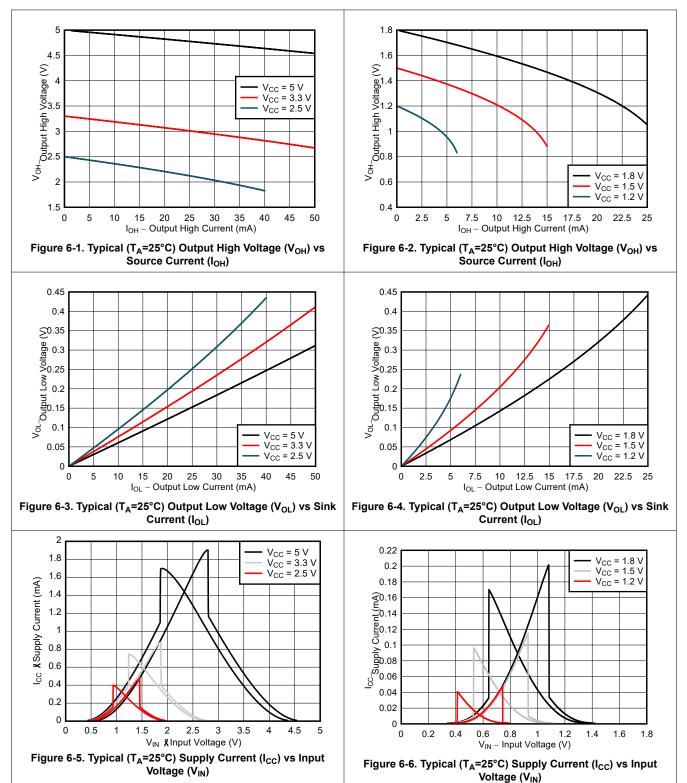
T<sub>A</sub> = 25°C <sup>(1)</sup>

				Su	pply Voltage	(V <sub>CCB</sub> = V <sub>CC</sub>	;A)			
	PARAMETER	Test Conditions	1.2 ± 0.1V	1.5 ± 0.1V	1.8 ± 0.15V	2.5 ± 0.2V	3.3 ± 0.3V	5.0 ± 0.5V	UNIT	
			TYP	TYP	TYP	TYP	TYP	TYP		
	A to B: outputs enabled	A Port	2	2	2	2	2	3		
C (2)	A to B: outputs disabled		CL = 0, RL = Open	2	2	2	2	2	3	pF
C <sub>pdA</sub> <sup>(2)</sup>	B to A: outputs enabled	f = 10 MHz	12	12	12	13	13	16	pr	
	B to A: outputs disabled	t <sub>rise</sub> = t <sub>fall</sub> = 1 ns	2	2	2	2	2	3		
	A to B: outputs enabled	R Port	12	12	12	13	13	16		
C (2)	A to B: outputs disabled	B Port CL = 0, RL = Open	2	2	2	2	2	3	pF	
C <sub>pdB</sub> <sup>(2)</sup>	B to A: outputs enabled		2	2	2	2	2	3	PL	
	B to A: outputs disabled	t <sub>rise</sub> = t <sub>fall</sub> = 1 ns	2	2	2	2	2	3		

For more information about power dissipation capacitance, see the *CMOS Power Consumption and C<sub>pd</sub> Calculation* application report.
 C<sub>pdA</sub> and C<sub>pdB</sub> are repectively A-Port and B-Port power dissipation capacitances per transceiver.



## 6.14 Typical Characteristics



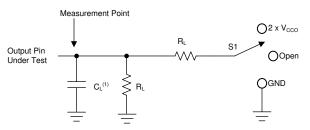


## 7 Parameter Measurement Information

## 7.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1 MHz
- Z<sub>O</sub> = 50 Ω
- Δt/ΔV ≤ 1 ns/V

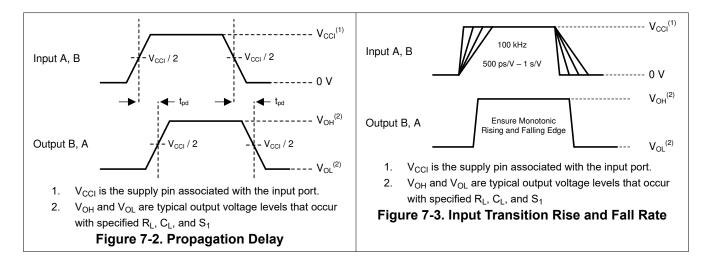


1.  $C_{L}$  includes probe and jig capacitance.

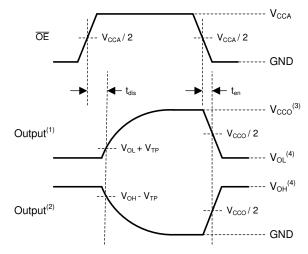
Figure 7-1. Load Circuit

	Parameter	V <sub>cco</sub>	RL	CL	S <sub>1</sub>	V <sub>TP</sub>						
t <sub>pd</sub>	Propagation (delay) time	1.1 V – 5.5 V	2 kΩ	15 pF	Open	N/A						
		1.1 V – 1.6 V	2 kΩ	15 pF	2 × V <sub>CCO</sub>	0.1 V						
t <sub>en</sub> , t <sub>dis</sub>	Enable time, disable time	1.65 V – 2.7 V	2 kΩ	15 pF	$2 \times V_{CCO}$	0.15 V						
		3.0 V – 5.5 V	2 kΩ	15 pF	$2 \times V_{CCO}$	0.3 V						
		1.1 V – 1.6 V	2 kΩ	15 pF	GND	0.1 V						
t <sub>en</sub> , t <sub>dis</sub>	t <sub>dis</sub> Enable time, disable time	1.65 V – 2.7 V	2 kΩ	15 pF	GND	0.15 V						
		3.0 V – 5.5 V	2 kΩ	15 pF	GND	0.3 V						









- 1. Output waveform on the condition that input is driven to a valid Logic Low.
- 2. Output waveform on the condition that input is driven to a valid Logic High.
- 3.  $V_{CCO}$  is the supply pin associated with the output port.
- 4.  $V_{OH} \mbox{ and } V_{OL} \mbox{ are typical output voltage levels with specified $R_L$, $C_L$, and $S_1$.}$

#### Figure 7-4. Enable Time And Disable Time



## 8 Detailed Description

### 8.1 Overview

The SN74LXC8T245 is an 8-bit translating transceiver that uses two individually configurable power-supply rails. The device is operational with both  $V_{CCA}$  and  $V_{CCB}$  supplies as low as 1.1 V and as high as 5.5 V. Additionally, the device can operate with  $V_{CCA} = V_{CCB}$ . The A port is designed to track  $V_{CCA}$ , and the B port is designed to track  $V_{CCB}$ .

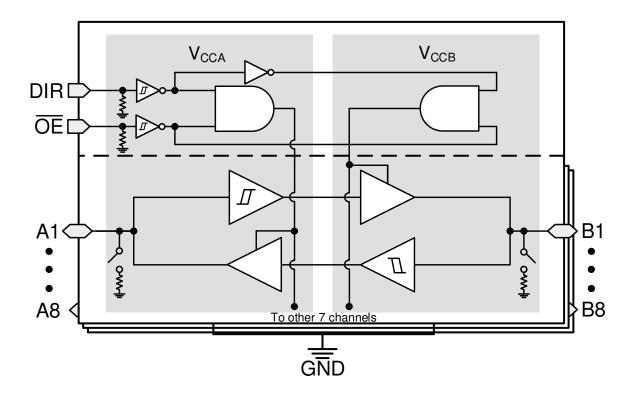
The SN74LXC8T245 device is designed for asynchronous communication between data buses, and transmits data from the A bus to the B bus or from the B bus to the A bus based on the logic level of the direction-control input (DIR). The output-enable input ( $\overline{OE}$ ) is used to disable the outputs so the buses are effectively isolated. The control pins of the SN74LXC8T245 (DIR and  $\overline{OE}$ ) are referenced to V<sub>CCA</sub>. For the level shifter I/Os to be in the high-impedance state during power up or power down, the  $\overline{OE}$  pin should be tied to V<sub>CCA</sub> through a pullup resistor.

This device is fully specified for partial-power-down applications using the  $I_{off}$  current. The  $I_{off}$  protection circuitry is designed so that no excessive current is drawn from or sourced into an input, output, or I/O while the device is powered down.

The V<sub>CC</sub> isolation or V<sub>CC</sub> disconnect feature is designed so that if either V<sub>CC</sub> is less than 100 mV or disconnected with the complementary supply within recommended operating conditions, both I/O ports are weakly pulled-down and then set to the high-impedance state by disabling their outputs while the supply current is maintained. The I<sub>off-float</sub> circuitry is designed so that no excessive current is drawn from or sourced into an input, output, or I/O while the supply is floating.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

#### 8.2 Functional Block Diagram





### 8.3 Feature Description

#### 8.3.1 CMOS Schmitt-Trigger Inputs with Integrated Pulldowns

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law ( $R = V \div I$ ).

The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the *Electrical Characteristics*, which makes this device extremely tolerant to slow or noisy inputs. Driving the inputs slowly will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, see the *Understanding Schmitt Triggers* application brief.

#### 8.3.1.1 I/Os with Integrated Dynamic Pull-Down Resistors

Input circuits of the data I/Os are always active even when the device is disabled. It is recommended to keep a valid voltage level at the I/Os to avoid high current consumption. To help avoid floating inputs on the I/Os during disabling, this device has 100-k $\Omega$  typical integrated weak dynamic pull-downs on all data I/Os. When the device is disabled, the dynamic pull-downs are activated for only a short period of time to help drive and keep low any floating inputs before the device I/Os become high impedance. If the I/O lines will be floated after the device is disabled, then it is recommended to keep them at a valid input voltage level using external pull-downs. This feature is ideal for loads of 30 pF or less. If greater capactive loading is present, then external pull-downs are recommended. If an external pull-up is required, then it should be no larger than 15 k $\Omega$  to avoid contention with the 100 k $\Omega$  internal pull-down.

#### 8.3.1.2 Control Inputs with Integrated Static Pull-Down Resistors

Similar to the data I/Os, floating control inputs can cause high current consumption. This device has integrated weak static pull-downs of 5-M $\Omega$  typical on the control inputs (DIR and  $\overline{OE}$ ) to help avoid this concern. These pull-downs are always present. For example, if the DIR pin is left floating, then the B port will be configured as an input and the A port will be configured as an output.

#### 8.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

#### 8.3.3 Partial Power Down (I<sub>off</sub>)

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I<sub>off</sub> in the *Electrical Characteristics*.



#### 8.3.4 V<sub>CC</sub> Isolation and V<sub>CC</sub> Disconnect (I<sub>off-float</sub>)

This device has *I/Os with Integrated Dynamic Pull-Down Resistors*. The I/Os will get pulled down and then enter a high-impedance state when either supply is < 100 mV or left floating (disconnected), while the other supply is still connected to the device. It is recommended that the I/Os for this device are not driven and kept at a logic low state prior to floating (disconnecting) either supply.

The maximum supply current is specified by  $I_{CCx}$ , while  $V_{CCx}$  is floating, in the *Electrical Characterstics*. The maximum leakage into or out of any input or output pin on the device is specified by  $I_{off(float)}$  in the *Electrical Characteristics*.

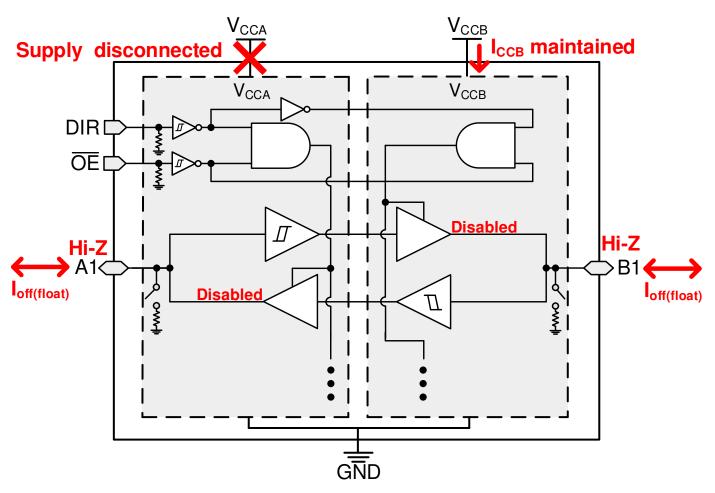


Figure 8-1. V<sub>CC</sub> Disconnect Feature

#### 8.3.5 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

#### 8.3.6 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to VCC when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

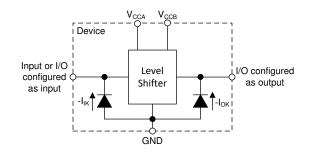


#### 8.3.7 Negative Clamping Diodes

Figure 8-2 shows how the inputs and outputs to this device have negative clamping diodes.

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



#### Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

#### 8.3.8 Fully Configurable Dual-Rail Design

Both the  $V_{CCA}$  and  $V_{CCB}$  pins can be supplied at any voltage from 1.1 V to 5.5 V, making the device suitable for translating between any of the voltage nodes (1.2 V, 1.5 V, 1.8 V, 3.3 V, and 5.0 V).

#### 8.3.9 Supports High-Speed Translation

The SN74LXC8T245 device can support high data-rate applications. The translated signal data rate can be up to 420 Mbps when the signal is translated from 3.3 V to 5.0 V.

#### 8.4 Device Functional Modes

CONTRO	L INPUTS	Port S	tatus	OPERATION						
ŌĒ	DIR	A PORT	B PORT	OPERATION						
L	L	Output (Enabled)	Input (Hi-Z)	B data to A bus						
L	Н	Input (Hi-Z)	Output (Enabled)	A data to B bus						
Н	Х	Input (Hi-Z)	Input (Hi-Z)	Isolation						

#### Table 8-1. Function Table<sup>(1)</sup>

(1) Input circuits of the data I/Os are always active and should be kept at a valid logic level.



## 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

The SN74LXC8T245 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74LXC8T245 device is ideal for use in applications where a push-pull driver is connected to the data I/Os. The maximum data rate can be up to 420 Mbps when device translates a signal from 3.3 V to 5.0 V.

#### 9.2 Typical Application

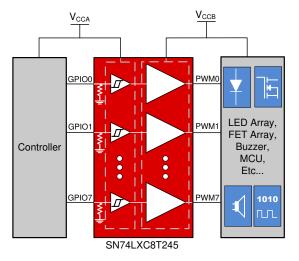


Figure 9-1. LED Driver Application

#### 9.2.1 Design Requirements

For this design example, use the parameters listed in Table 9-1.

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.1 V to 5.5 V
Output voltage range	1.1 V to 5.5 V

#### 9.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range
  - Use the supply voltage of the device that is driving the SN74LXC8T245 device to determine the input voltage range. For a valid logic-high, the value must exceed the positive-going input-threshold voltage (V<sub>t+</sub>) of the input port. For a valid logic low the value must be less than the negative-going input-threshold voltage (V<sub>t-</sub>) of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN74LXC8T245 device is driving to determine the output voltage range.



## **10 Power Supply Recommendations**

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices, as described in *Glitch-free Power Supply Sequencing*.

## 11 Layout

#### **11.1 Layout Guidelines**

For device reliability, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1 μF capacitor is recommended, but transient performance can be improved by having both 1 μF and 0.1 μF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing.

### 11.2 Layout Example

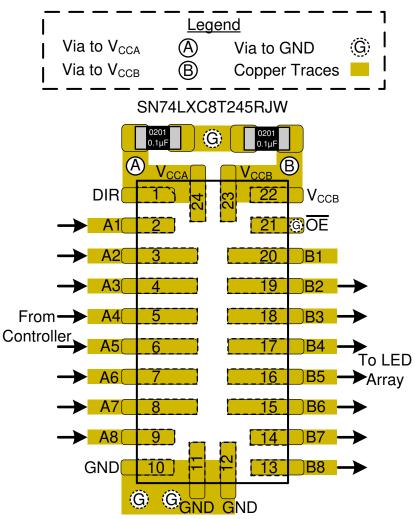


Figure 11-1. Layout Example – SN74LXC8T245RJW



## 12 Device and Documentation Support

### 12.1 Device Support

#### **12.1.1 Regulatory Requirements**

No statutory or regulatory requirements apply to this device.

There are no special characteristics for this product.

#### **12.2 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **12.3 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 12.4 Trademarks

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#### 12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### **PACKAGING INFORMATION**

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
SN74LXC8T245DGSR	Active	Production	VSSOP (DGS)   24	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L8T245
SN74LXC8T245DGSR.A	Active	Production	VSSOP (DGS)   24	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L8T245
SN74LXC8T245DGSR.B	Active	Production	VSSOP (DGS)   24	5000   LARGE T&R	-	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L8T245
SN74LXC8T245PWR	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245PWR.A	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245PWRG4	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245PWRG4.A	Active	Production	TSSOP (PW)   24	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245RHLR	Active	Production	VQFN (RHL)   24	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245RHLR.A	Active	Production	VQFN (RHL)   24	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245RHLRG4	Active	Production	VQFN (RHL)   24	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245
SN74LXC8T245RHLRG4.A	Active	Production	VQFN (RHL)   24	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LX8T245

<sup>(1)</sup> **Status:** For more details on status, see our product life cycle.

<sup>(2)</sup> **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.



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# PACKAGE OPTION ADDENDUM

24-Jul-2025

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#### OTHER QUALIFIED VERSIONS OF SN74LXC8T245 :

• Automotive : SN74LXC8T245-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



Texas

STRUMENTS

### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LXC8T245DGSR	VSSOP	DGS	24	5000	330.0	16.4	5.44	6.4	1.45	8.0	16.0	Q1
SN74LXC8T245RHLR	VQFN	RHL	24	3000	330.0	12.4	3.8	5.8	1.2	8.0	12.0	Q1
SN74LXC8T245RHLRG4	VQFN	RHL	24	3000	330.0	12.4	3.8	5.8	1.2	8.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

24-Jul-2025



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LXC8T245DGSR	VSSOP	DGS	24	5000	353.0	353.0	32.0
SN74LXC8T245RHLR	VQFN	RHL	24	3000	367.0	367.0	35.0
SN74LXC8T245RHLRG4	VQFN	RHL	24	3000	367.0	367.0	35.0

# **PW0024A**



# **PACKAGE OUTLINE**

# TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



# PW0024A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# PW0024A

# **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

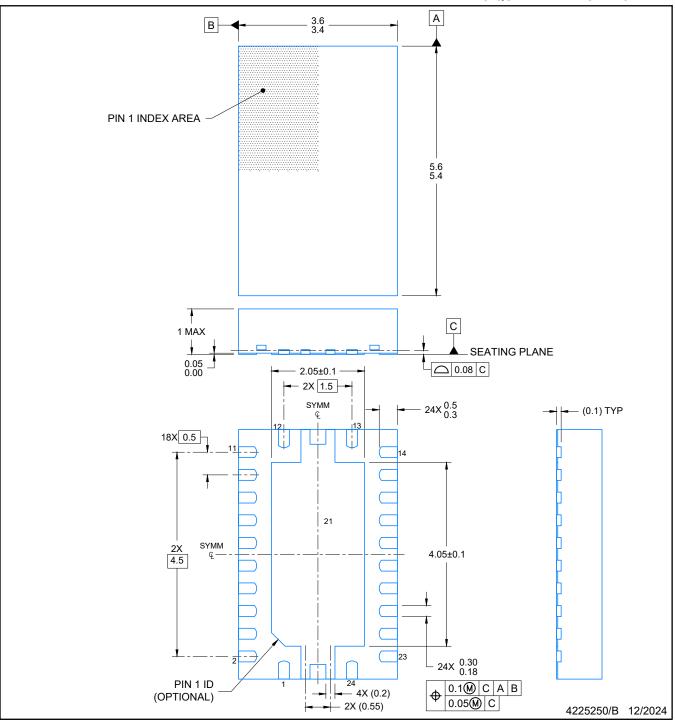


# **RHL0024A**

# **PACKAGE OUTLINE**

# VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

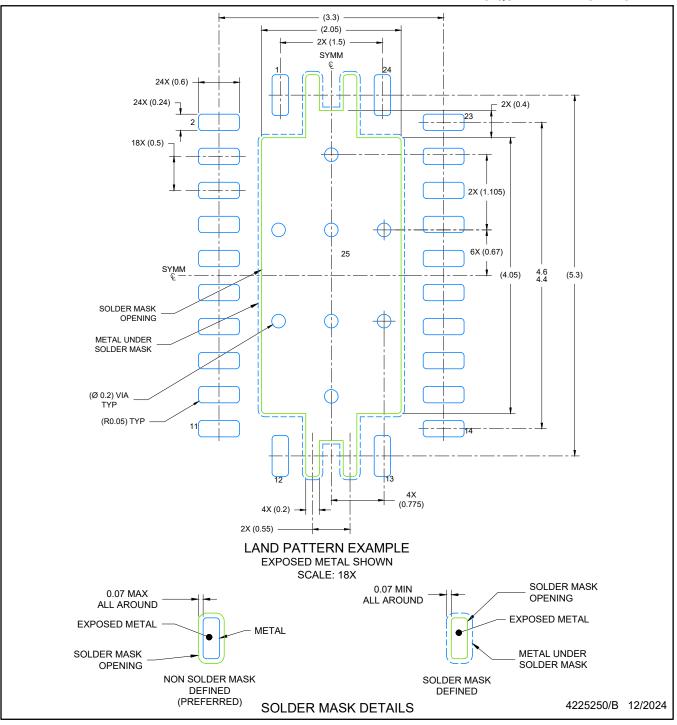


# **RHL0024A**

# **EXAMPLE BOARD LAYOUT**

# VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

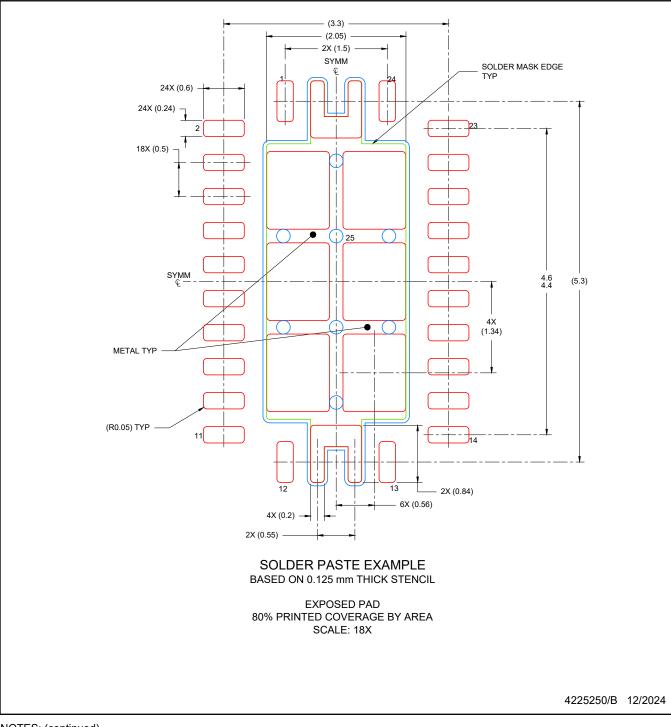


# **RHL0024A**

# **EXAMPLE STENCIL DESIGN**

# VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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